

DOCKET NO. 8229-014-27



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Krishnaswamy RAMKUMAR, et al. ART UNIT: 2813

SERIAL NO.: 09/975,256

EXAMINER: David L. Hogans

FILING DATE: October 12, 2001

FOR: METHOD FOR GROWING ULTRA THIN NITRIDED OXIDE

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the outstanding Office Action dated January 23, 2003, entry of the following amendments is respectfully requested.

IN THE SPECIFICATION

Delete the second full paragraph at page 3, lines 8-21, and insert therefor the following:

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--Various nitrogen containing gases have been employed for thermal nitridation and oxynitride deposition, including N₂, NH₃, NO and N₂O. See, for example, United States Patent Nos. 5,403,786; 5,521,127; 5,629,221; and 5,880,040. See also Gusev, et al., "Growth and Characterization of Ultrathin Nitrided Silicon Oxide Films", in IBM J. Res. Develop., Vol. 43, No. 3, May 1999, pp. 265-286; Hook, et al., "Nitrided Gate Oxides for 3.3-V Logic Application: Reliability and Device Design Considerations", in IBM J. Res. Develop., Vol. 43, No. 3, May 1999, pp. 393-406; and Buchanan, "Scaling the Gate Dielectric: Materials, Integration and Reliability", in IBM J. Res. Develop., Vol. 43, No. 3, May 1999, pp. 245-264. Hogans, et al. disclose a high pressure (15 to 25 atm.) process for oxynitride gate formation using nitric oxide gas.

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